



BUL654

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

PRELIMINARY DATA

- HIGH VOLTAGE CAPABILITY
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- LOW BASE-DRIVE REQUIREMENTS
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C

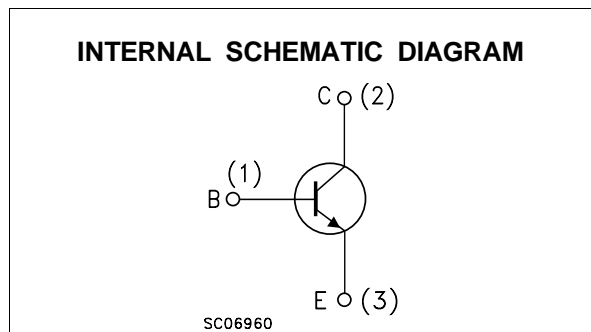
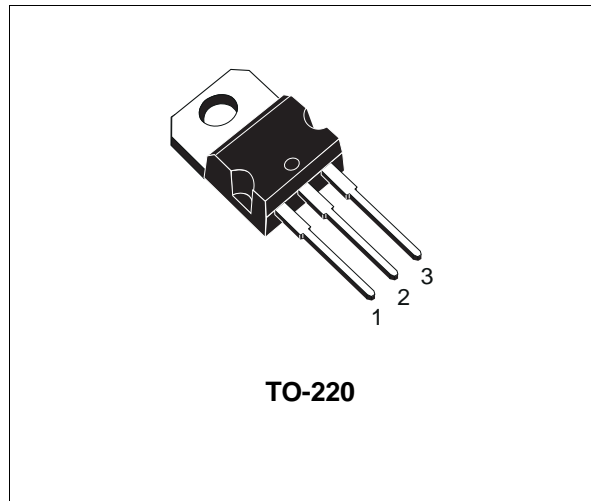
APPLICATIONS

- ELECTRONIC TRANSFORMER FOR HALOGEN LAMPS
- SWITCH MODE POWER SUPPLIES

DESCRIPTION

The BUL654 is manufactured using high voltage Multi Epitaxial Planar technology for cost-effective high performance. It uses a Hollow Emitter structure to enhance switching speeds.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	700	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	9	V
I_C	Collector Current	12	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	18	A
I_B	Base Current	6	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	9	A
P_{tot}	Total Dissipation at $T_c = 25$ °C	80	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

BUL654

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-Case	Max	1.25	$^{\circ}C/W$
----------------	----------------------------------	-----	------	---------------

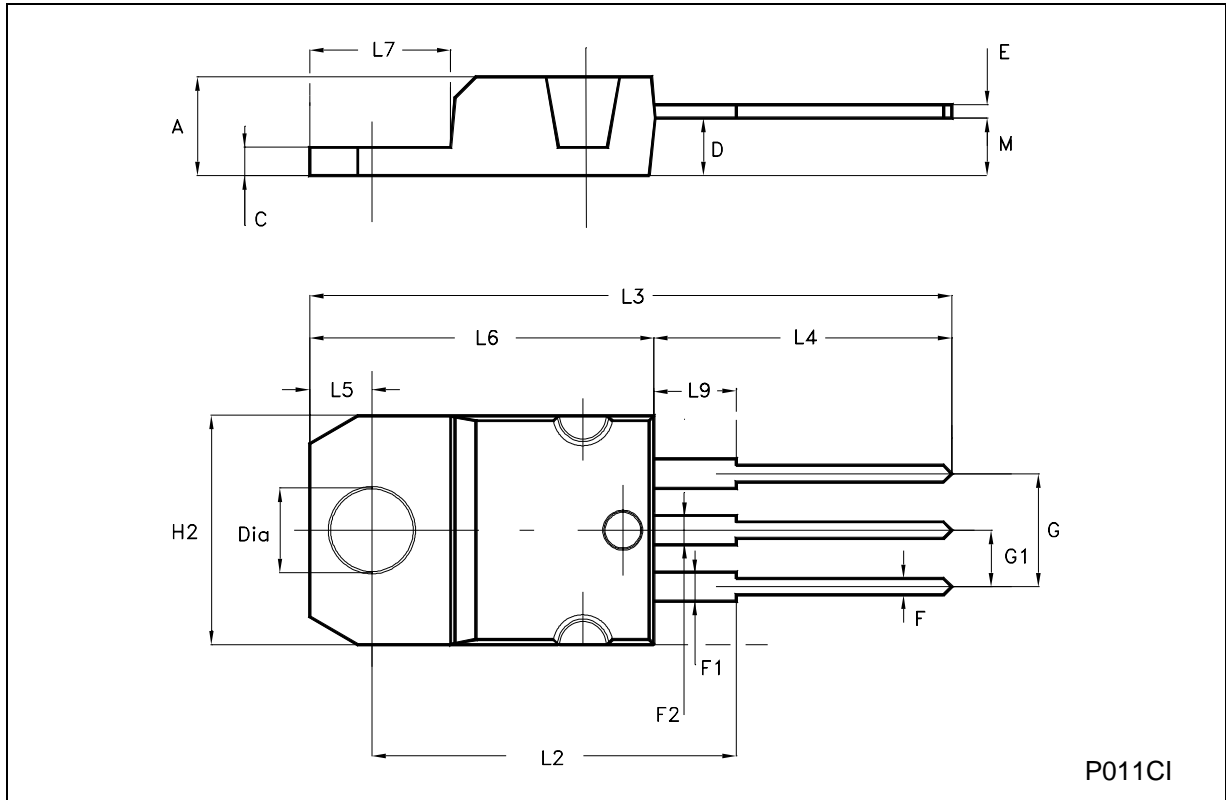
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = 700 V$ $V_{CE} = 700 V$ $T_c = 125^{\circ}C$			50 500	μA μA
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 400 V$			100	μA
$V_{CEO(sus)*}$	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 100 mA$ $L = 25 mH$	400			V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	$I_E = 10 mA$	9			V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 2 A$ $I_B = 0.4 A$ $I_C = 7 A$ $I_B = 1.4 A$		0.15 0.35	0.3 0.7	V V
$V_{BE(sat)*}$	Base-Emitter Saturation Voltage	$I_C = 2 A$ $I_B = 0.4 A$ $I_C = 7 A$ $I_B = 1.4 A$		0.85 1	1 1.2	V V
h_{FE*}	DC Current Gain	$I_C = 10 mA$ $V_{CE} = 2 V$ $I_C = 2 A$ $V_{CE} = 2 V$ $I_C = 6 A$ $V_{CE} = 2 V$ $I_C = 12 A$ $V_{CE} = 5 V$	15 15 7 4			

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
M		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2003 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>